

Effect of Oxygen Plasma and Growth Temperature on the Densification of Plasma-Enhanced Atomic Layer Deposited Silicon Dioxide Film

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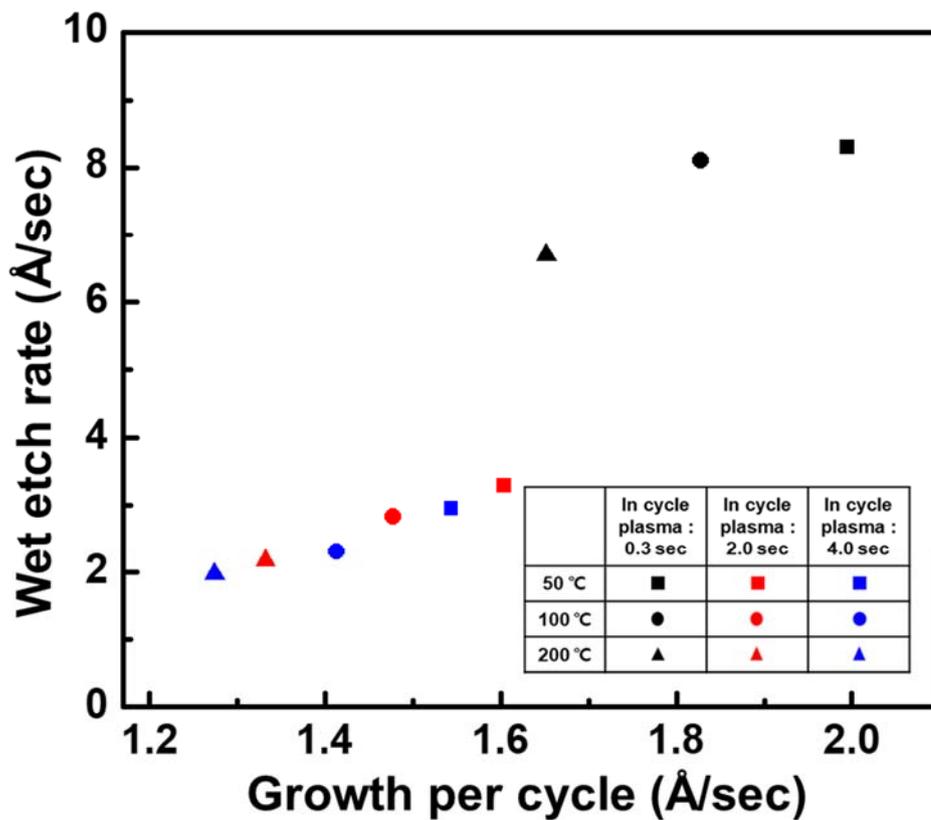


Fig 1. WER and GPC of PE-ALD SiO₂ films along with varying in-cycle plasma time and growth temperature.